Low Capacitance, Low Charge Injection, ±15 V/12 V *i*CMOS SPDT in SOT-23

ADG1219

FEATURES

<0.5 pC charge injection over full signal range
2.5 pF off capacitance
Low leakage; 0.6 nA maximum @ 85°C
120 Ω on resistance
Fully specified at +12 V, ±15 V
No V_L supply required
3 V logic-compatible inputs
Rail-to-rail operation
8-lead SOT-23 package

APPLICATIONS

Automatic test equipment
Data acquisition systems
Battery-powered systems
Sample-and-hold systems
Audio/video signal routing
Communication systems

FUNCTIONAL BLOCK DIAGRAM

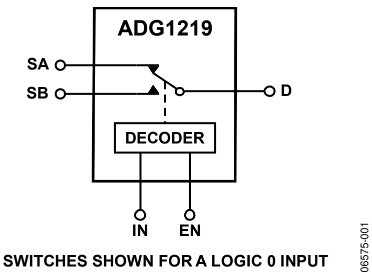

Figure 1.

GENERAL DESCRIPTION

The ADG1219 is a monolithic *i*CMOS® device containing an SPDT switch. An EN input is used to enable or disable the device. When disabled, all channels are switched off. When on, each channel conducts equally well in both directions and has an input signal range that extends to the supplies. Each switch exhibits break-before-make switching action.

The *i*CMOS (industrial CMOS) modular manufacturing process combines high voltage complementary metal-oxide semiconductor (CMOS) and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no other generation of high voltage parts has been able to achieve. Unlike analog ICs using conventional CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and reduced package size.

The ultralow capacitance and exceptionally low charge injection of these multiplexers make them ideal solutions for data acquisition and sample-and-hold applications, where low glitch and fast settling are required. Figure 2 shows that there is minimum charge injection over the entire signal range of the device. *i*CMOS construction also ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

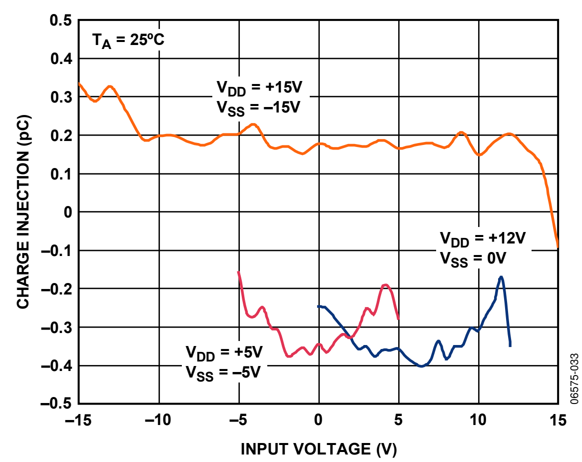

Figure 2. Charge Injection vs. Input Voltage

Rev. A

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3/09—Rev. 0 to Rev. A

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4/08—Revision 0: Initial Version

SPECIFICATIONS

DUAL SUPPLY

V_{DD} = 15 V ± 10%, V_{SS} = −15 V ± 10%, GND = 0 V, unless otherwise noted.

Table 1.

Parameters	B Version[1] 25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance, R_{ON}	120			Ω typ	V_S = ±10 V, I_S = −1 mA; see Figure 23
	200	240	270	Ω max	V_{DD} = +13.5 V, V_{SS} = −13.5 V
On Resistance Match Between Channels, ΔR_{ON}	3.5			Ω typ	V_S = ±10 V, I_S = −1 mA
	6	10	12	Ω max	
On Resistance Flatness, $R_{FLAT(ON)}$	20			Ω typ	V_S = −5 V, 0 V, +5 V; I_S = −1 mA
	64	76	84	Ω max	
LEAKAGE CURRENTS					V_{DD} = +16.5 V, V_{SS} = −16.5 V
Source Off Leakage, I_S (Off)	±0.004			nA typ	V_S = ±10 V, V_S = ±10 V; see Figure 24
	±0.1	±0.6	±1	nA max	
Drain Off Leakage, I_D (Off)	±0.009			nA typ	V_S = ±10 V, V_S = ±10 V; see Figure 24
	±0.1	±0.6	±1	nA max	
Channel On Leakage, I_D, I_S (On)	±0.02			nA typ	V_S = V_D = ±10 V; see Figure 25
	±0.2	±0.6	±1	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.005			μA typ	V_{IN} = V_{INL} or V_{INH}
			±0.1	μA max	
Digital Input Capacitance, C_{IN}	2			pF typ	
DYNAMIC CHARACTERISTICS[2]					
Transition Time, $t_{TRANSITION}$	140			ns typ	R_L = 300 Ω, C_L = 35 pF
	170	200	230	ns max	V_S = 10 V; see Figure 30
t_{ON} (EN)	85			ns typ	R_L = 300 Ω, C_L = 35 pF
	105	130	140	ns max	V_S = 10 V; see Figure 30
t_{OFF} (EN)	105			ns typ	R_L = 300 Ω, C_L = 35 pF
	125	150	170	ns max	V_S = 10 V; see Figure 30
Break-Before-Make Time Delay, t_{BBM}	40			ns typ	R_L = 300 Ω, C_L = 35 pF
			10	ns min	V_{S1} = V_{S2} = 10 V; see Figure 31
Charge Injection	0.1			pC typ	V_S = 0 V, R_S = 0 Ω, C_L = 1 nF; see Figure 32
Off Isolation	77			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	80			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 27
Total Harmonic Distortion + Noise	0.15			% typ	R_L = 10 kΩ, 5 V rms, f = 20 Hz to 20 kHz
−3 dB Bandwidth	520			MHz typ	R_L = 50 Ω, C_L = 5 pF; see Figure 28
C_S (Off)	2.5			pF typ	f = 1 MHz; V_S = 0 V
	3.3			pF max	f = 1 MHz; V_S = 0 V
C_D (Off)	4.3			pF typ	f = 1 MHz; V_S = 0 V
	5.1			pF max	f = 1 MHz; V_S = 0 V
C_D, C_S (On)	7.5			pF typ	f = 1 MHz; V_S = 0 V
	10			pF max	f = 1 MHz; V_S = 0 V

Parameters	B Version[1] 25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
POWER REQUIREMENTS					V_{DD} = +16.5 V, V_{SS} = −16.5 V
I_{DD}	0.001			μA typ	Digital inputs = 0 V or V_{DD}
			1.0	μA max	
I_{DD}	140			μA typ	Digital inputs = 5 V
			190	μA max	
I_{SS}	0.001			μA typ	Digital inputs = 0 V, 5 V or V_{DD}
			1.0	μA max	
V_{DD}/V_{SS}			±5/±16.5	V min/max	$\lvert V_{DD}\rvert = \lvert V_{SS}\rvert$

[1] Temperature range for B version is −40°C to +125°C.
[2] Guaranteed by design; not subject to production test.

SINGLE SUPPLY

V_{DD} = 12 V ± 10%, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 2.

Parameters	B Version[1] 25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance, R_{ON}	300			Ω typ	V_S = 0 V to 10 V, I_S = −1 mA; see Figure 23
	475	567	625	Ω max	V_{DD} = 10.8 V, V_{SS} = 0 V
On Resistance Match Between Channels, ΔR_{ON}	4.5			Ω typ	V_S = 0 V to 10 V, I_S = −1 mA
	16	26	27	Ω max	
On Resistance Flatness, $R_{FLAT(ON)}$	60			Ω typ	V_S = 3 V, 6 V, 9 V, I_S = −1 mA
LEAKAGE CURRENTS					V_{DD} = 13.2 V
Source Off Leakage, I_S (Off)	±0.006			nA typ	V_S = 1 V/10 V, V_D = 10 V/1 V; see Figure 24
	±0.1	±0.6	±1	nA max	
Drain Off Leakage, I_D (Off)	±0.006			nA typ	V_S = 1 V/10 V, V_D = 10 V/1 V; see Figure 24
	±0.1	±0.6	±1	nA max	
Channel On Leakage, I_D, I_S (On)	±0.02			nA typ	V_S = V_D = 1 V or 10 V; see Figure 25
	±0.2	±0.6	±1	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.001			μA typ	V_{IN} = V_{INL} or V_{INH}
			±0.1	μA max	
Digital Input Capacitance, C_{IN}	3			pF typ	
DYNAMIC CHARACTERISTICS[2]					
Transition Time, $t_{TRANSITION}$	195			ns typ	R_L = 300 Ω, C_L = 35 pF
	250	300	340	ns max	V_S = 8 V; see Figure 30
t_{ON} (EN)	120			ns typ	R_L = 300 Ω, C_L = 35 pF
	150	190	210	ns max	V_S = 8 V; see Figure 30
t_{OFF} (EN)	145			ns typ	R_L = 300 Ω, C_L = 35 pF
	185	220	255	ns max	V_S = 8 V; see Figure 30
Break-Before-Make Time Delay, t_{BBM}	70			ns typ	R_L = 300 Ω, C_L = 35 pF
			10	ns min	V_{S1} = V_{S2} = 8 V; see Figure 31
Charge Injection	−0.8			pC typ	V_S = 6 V, R_S = 0 Ω, C_L = 1 nF; see Figure 32
Off Isolation	80			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 26
Channel-to-Channel Crosstalk	80			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz; see Figure 27
−3 dB Bandwidth	400			MHz typ	R_L = 50 Ω, C_L = 5 pF; see Figure 28

Parameters	B Version[1] 25°C	−40°C to +85°C	−40°C to +125°C	Unit	Test Conditions/Comments
C_S (Off)	2.9			pF typ	f = 1 MHz; V_S = 6 V
	3.7			pF max	f = 1 MHz; V_S = 6 V
C_D (Off)	5			pF typ	f = 1 MHz; V_S = 6 V
	5.8			pF max	f = 1 MHz; V_S = 6 V
C_D, C_S (On)	8.5			pF typ	f = 1 MHz; V_S = 6 V
	11			pF max	f = 1 MHz; V_S = 6 V
POWER REQUIREMENTS					V_{DD} = 13.2 V
I_{DD}	0.001			μA typ	Digital inputs = 0 V or V_{DD}
			1.0	μA max	
I_{DD}	140			μA typ	Digital inputs = 5 V
			190	μA max	
V_{DD}			5/16.5	V min/max	V_{SS} = 0 V, GND = 0 V

[1] Temperature range for B version is −40°C to +125°C.
[2] Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted.

Table 3.

Parameter	Rating
V_{DD} to V_{SS}	35 V
V_{DD} to GND	−0.3 V to +25 V
V_{SS} to GND	+0.3 V to −25 V
Analog Inputs[1]	V_{SS} − 0.3 V to V_{DD} + 0.3 V or 30 mA, whichever occurs first
Digital Inputs[1]	GND − 0.3 V to V_{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, S or D	100 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current per Channel, S or D	30 mA
Operating Temperature Range	
Industrial (B Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
8-Lead SOT-23, θ_{JA} Thermal Impedance	211.5°C/W
Reflow Soldering Peak Temperature, Pb Free	260°C

[1] Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

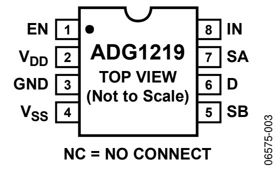

Figure 3. SOT-23 Pin Configuration

Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	EN	Active High Digital Input. When this pin is low, the device is disabled and all switches are turned off. When this pin is high, the IN logic input determines which switch is turned on.
2	V_{DD}	Most Positive Power Supply Potential.
3	GND	Ground (0 V) Reference.
4	V_{SS}	Most Negative Power Supply Potential.
5	SB	Source Terminal. Can be an input or output.
6	D	Drain Terminal. Can be an input or output.
7	SA	Source Terminal. Can be an input or output.
8	IN	Logic Control Input.

Table 5. Truth Table

EN	IN	Switch A	Switch B
0	X	Off	Off
1	0	On	Off
1	1	Off	On

TYPICAL PERFORMANCE CHARACTERISTICS

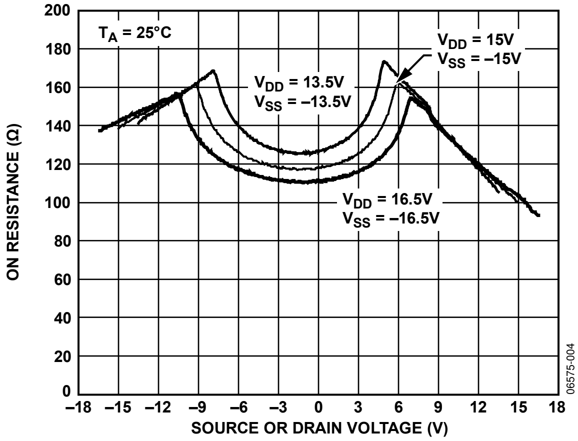

Figure 4. On Resistance as a Function of V_D (V_S) for Dual Supply

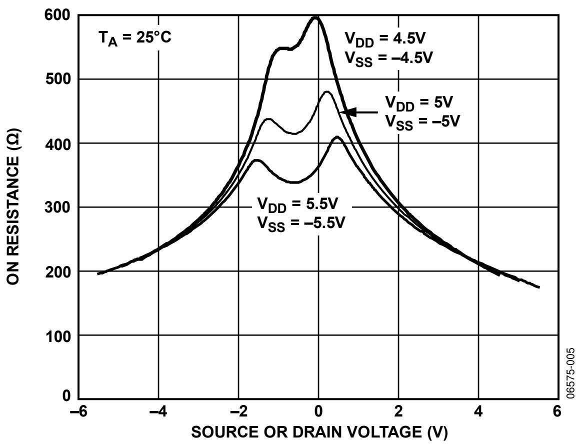

Figure 5. On Resistance as a Function of V_D (V_S) for Dual Supply

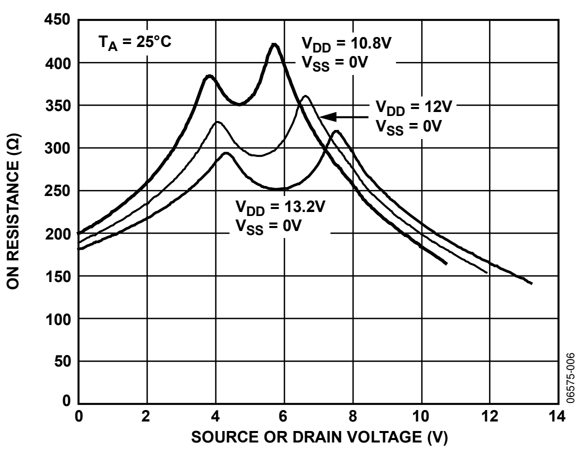

Figure 6. On Resistance as a Function of V_D (V_S) for Single Supply

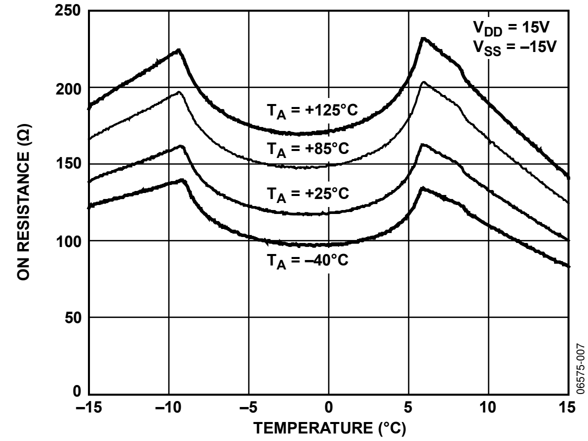

Figure 7. On Resistance as a Function of V_D (V_S) for Different Temperatures, Dual Supply

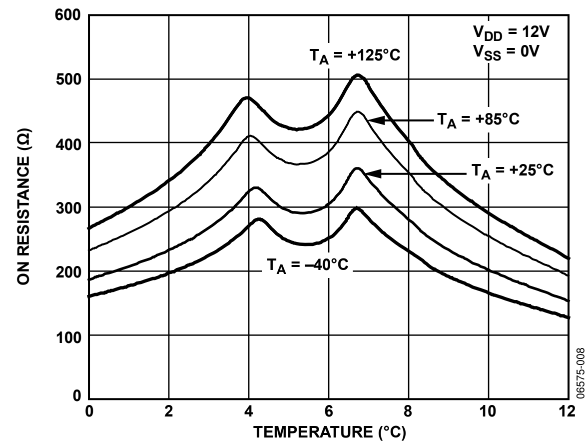

Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures, Single Supply

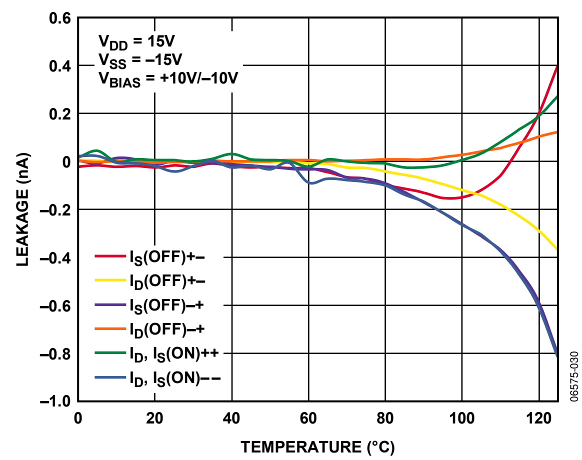

Figure 9. Leakage Currents as a Function of Temperature, 15 V Dual Supply

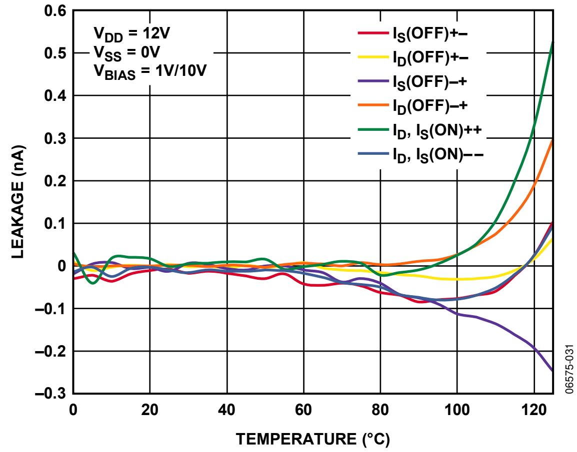

Figure 10. Leakage Currents as a Function of Temperature, 12 V Single Supply

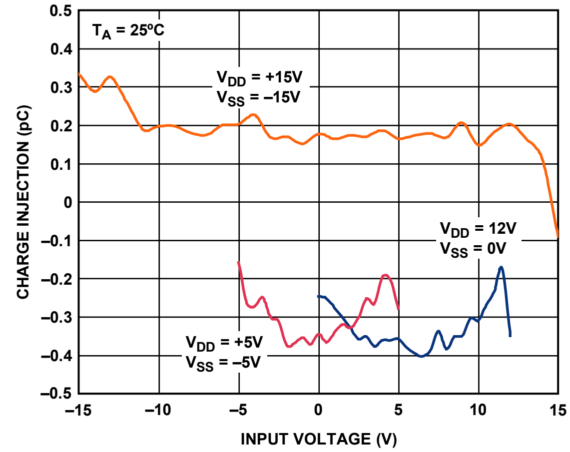

Figure 13. Charge Injection vs. Input Voltage

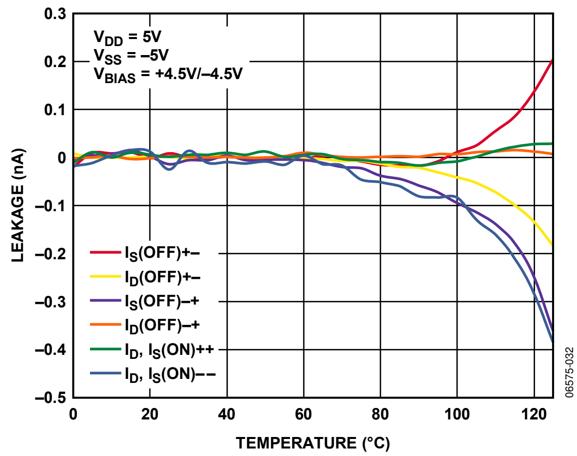

Figure 11. Leakage Currents as a Function of Temperature, 5 V Dual Supply

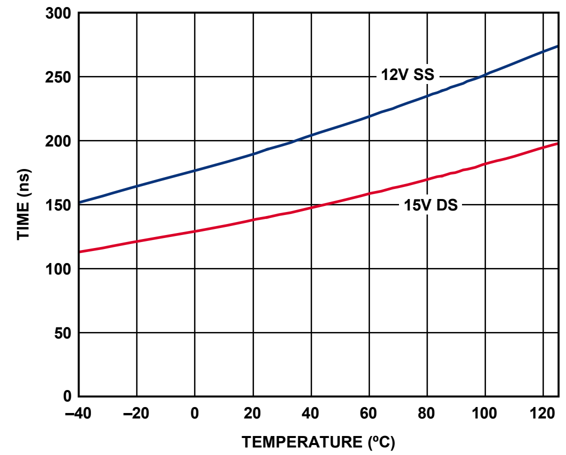

Figure 14. $t_{TRANSITION}$ Time vs. Temperature

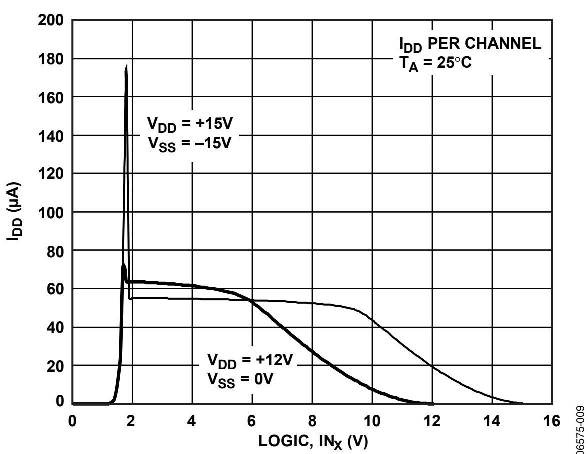

Figure 12. I_{DD} vs. Logic Level

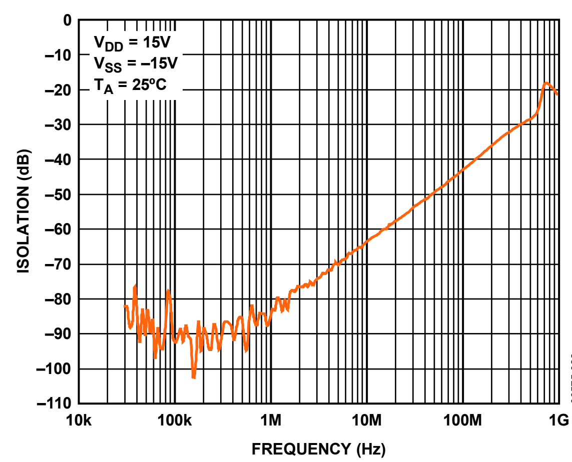

Figure 15. Off Isolation vs. Frequency

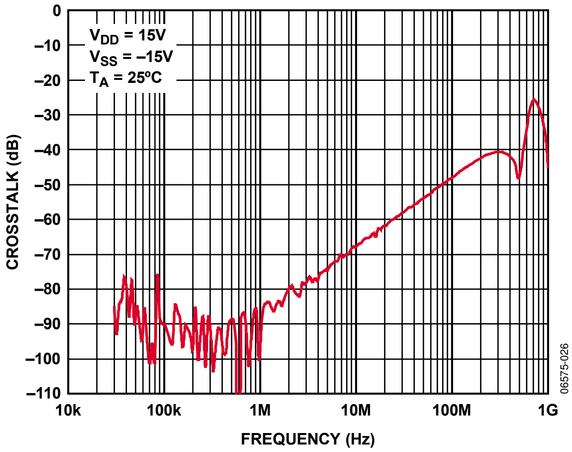

Figure 16. Crosstalk vs. Frequency

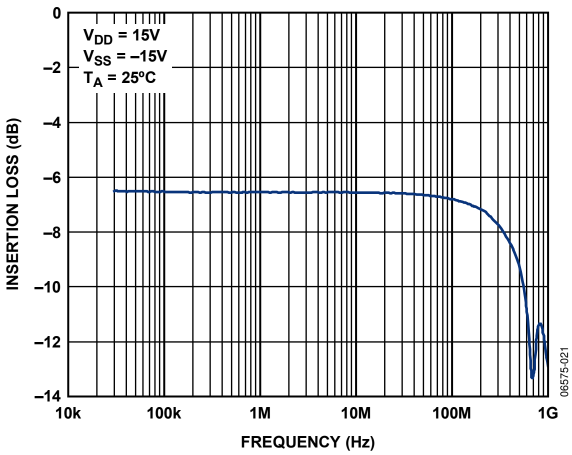

Figure 17. On Response vs. Frequency

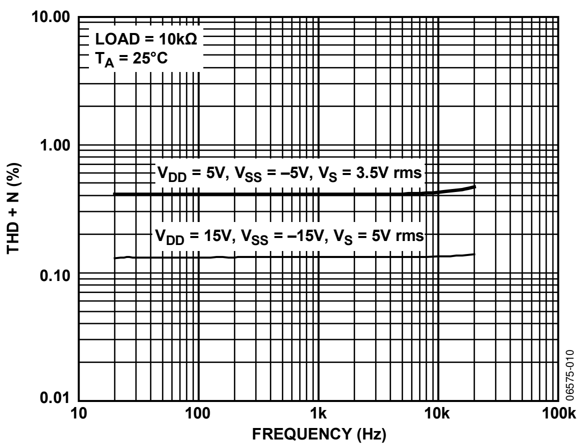

Figure 18. THD + N vs. Frequency

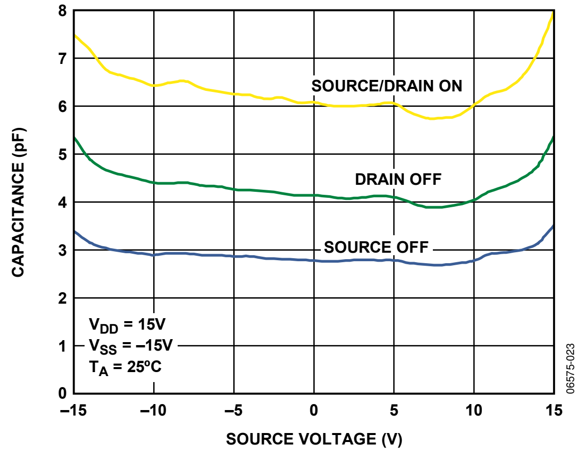

Figure 19. Capacitance vs. Source Voltage for Dual Supply

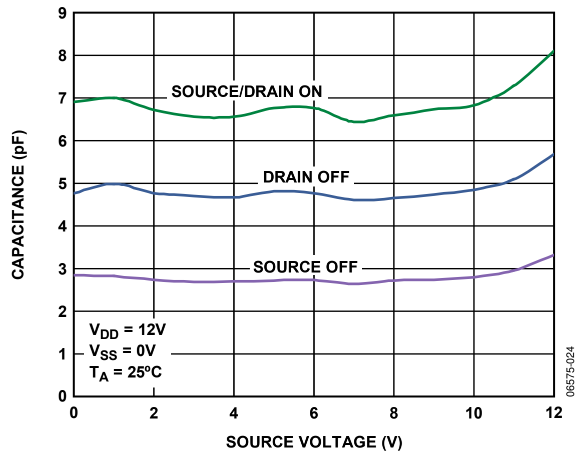

Figure 20. Capacitance vs. Source Voltage for Single Supply

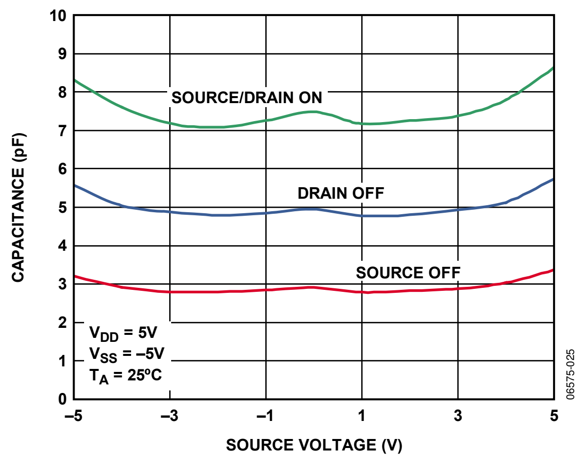

Figure 21. Capacitance vs. Source Voltage for Dual Supply

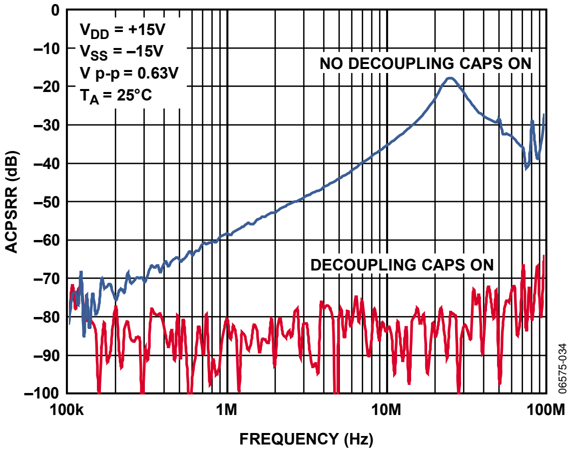

Figure 22. ACPSRR vs. Frequency

TEST CIRCUITS

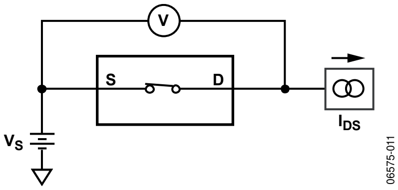

Figure 23. On Resistance

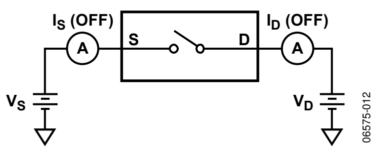

Figure 24. Off Leakage

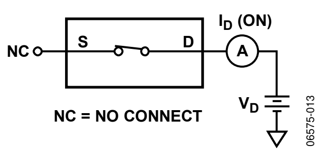

Figure 25. On Leakage

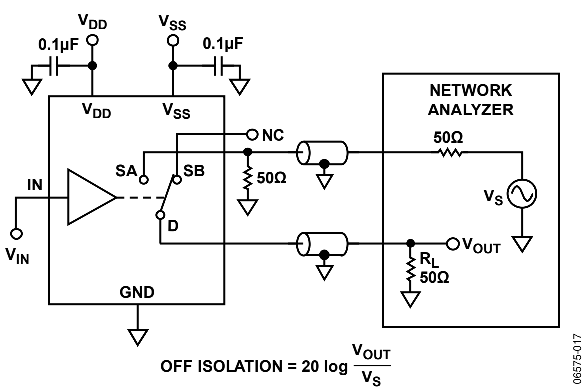

Figure 26. Off Isolation

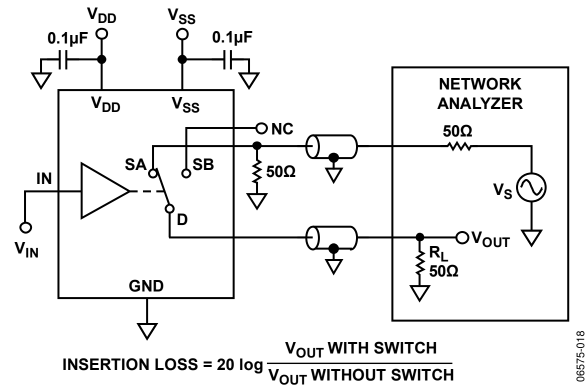

Figure 27. Channel-to-Channel Crosstalk

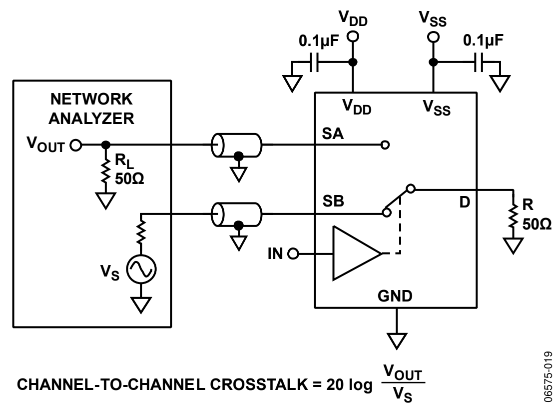

Figure 28. Bandwidth

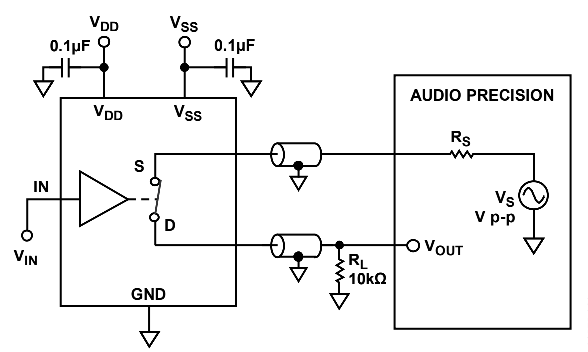

Figure 29. THD + Noise

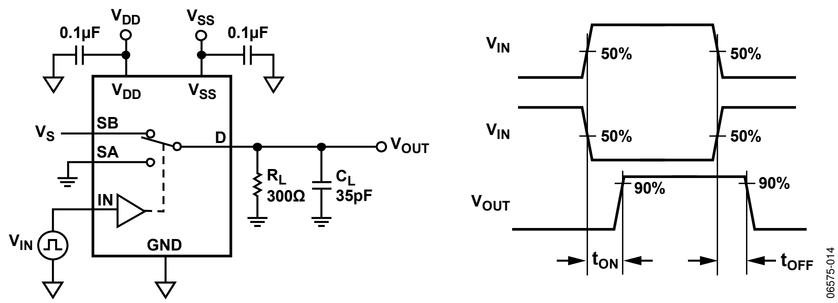

Figure 30. Switching Times

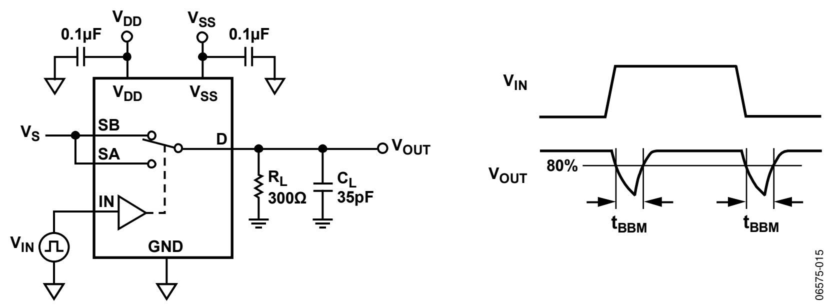

Figure 31. Break-Before-Make Time Delay

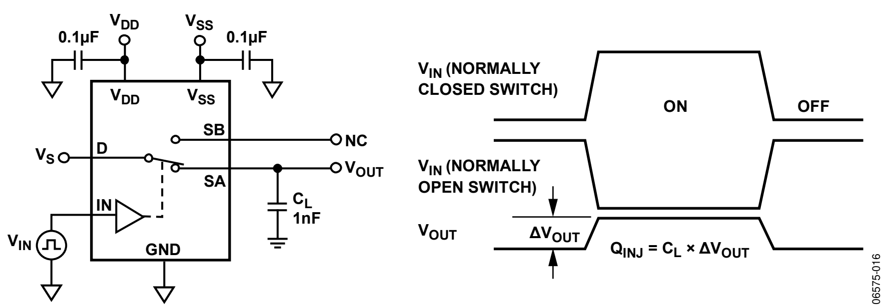

Figure 32. Charge Injection

TERMINOLOGY

I_{DD}
The positive supply current.

I_{SS}
The negative supply current.

V_D (V_S)
The analog voltage on Terminal D and Terminal S.

R_{ON}
The ohmic resistance between Terminal D and Terminal S.

$R_{FLAT(ON)}$
Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

I_S (Off)
The source leakage current with the switch off.

I_D (Off)
The drain leakage current with the switch off.

I_D, I_S (On)
The channel leakage current with the switch on.

V_{INL}
The maximum input voltage for Logic 0.

V_{INH}
The minimum input voltage for Logic 1.

I_{INL} (I_{INH})
The input current of the digital input.

C_S (Off)
The off switch source capacitance, measured with reference to ground.

C_D (Off)
The off switch drain capacitance, measured with reference to ground.

C_D, C_S (On)
The on switch capacitance, measured with reference to ground.

C_{IN}
The digital input capacitance.

t_{ON} (EN)
Delay time between the 50% and 90% points of the digital input and switch on condition.

t_{OFF} (EN)
Delay time between the 50% and 90% points of the digital input and switch off condition.

$t_{TRANSITION}$
Delay time between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

T_{BBM}
Off time measured between the 80% point of both switches when switching from one address state to another.

Charge Injection
A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation
A measure of unwanted signal coupling through an off switch.

Crosstalk
A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth
The frequency at which the output is attenuated by 3 dB.

On Response
The frequency response of the on switch.

Insertion Loss
The loss due to the on resistance of the switch.

Total Harmonic Distortion (THD + N)
The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

AC Power Supply Rejection Ratio (ACPSRR)
Measures the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of signal on the output to the amplitude of the modulation is the ACPSRR.

OUTLINE DIMENSIONS

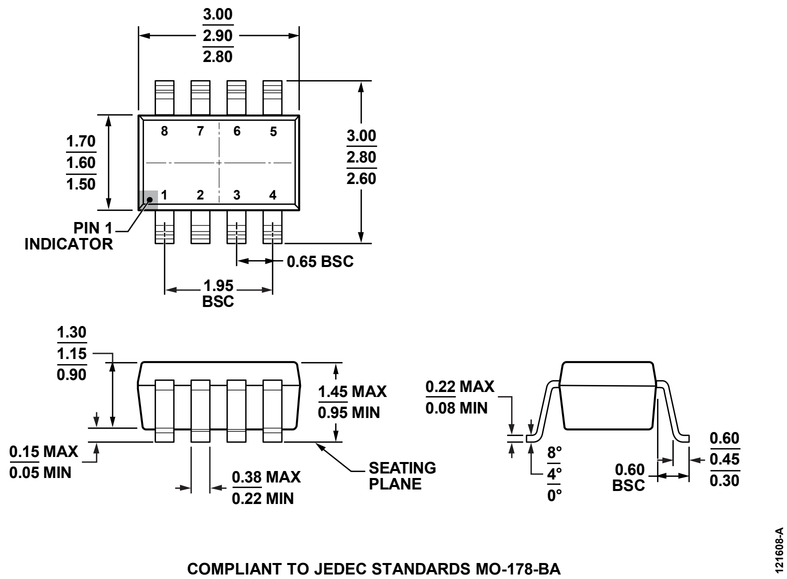

Figure 33. 8-Lead Lead Small Outline Transistor Package [SOT-23]
(RJ-8)
Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG1219BRJZ-R2[1]	−40°C to +125°C	8-Lead Lead Small Outline Transistor Package [SOT-23]	RJ-8	S24
ADG1219BRJZ-REEL7[1]	−40°C to +125°C	8-Lead Lead Small Outline Transistor Package [SOT-23]	RJ-8	S24

[1] Z = RoHS Compliant Part.

NOTES